

In the Claims:

1. 1. (currently amended) A method of manufacturing single-crystal semiconductor blocks, wherein small-diameter single-crystal semiconductor blocks [[2a]] of a relatively small diameter for slicing off single-crystal semiconductor wafers of a relatively small diameter desired by users are cut out from a large-diameter single-crystal semiconductor block [[1a]] of a relatively large diameter.
1. 2. (original) The method of manufacturing single-crystal semiconductor blocks according to claim 1, wherein said semiconductor is a III-V group compound semiconductor.
1. 3. (original) The method of manufacturing single-crystal semiconductor blocks according to claim 1, wherein said large-diameter single-crystal semiconductor block has a thickness of at least 10 mm.
1. 4. (original) The method of manufacturing single-crystal semiconductor blocks according to claim 1, wherein said small-diameter single-crystal semiconductor blocks are cut out by any of an electric discharge machining method, a wire saw method, a grinding method by means of a cylindrical core, and a band saw method.

1 5. (currently amended) The method of manufacturing single-  
2 crystal semiconductor blocks according to claim 1, wherein  
3 at least four said ~~small-scale~~ small-diameter  
4 single-crystal semiconductor blocks having a diameter of at  
5 least 2 inches are cut out from said ~~large-scale~~  
6 large-diameter single-crystal semiconductor block having a  
7 diameter of at least 5 inches.

1 6. (currently amended) The method of manufacturing  
2 single-crystal semiconductor blocks according to claim 1,  
3 wherein a total cross-sectional area of a plurality of said  
4 small-diameter single-crystal semiconductor blocks cut out  
5 from said ~~large-scale~~ large-diameter single-crystal  
6 semiconductor block corresponds to at least 50% of a  
7 cross-sectional area of said ~~large-scale~~ large-diameter  
8 single-crystal semiconductor block.

1 7. (original) The method of manufacturing single-crystal  
2 semiconductor blocks according to claim 1, wherein  
3 defective parts included in any cross-sectional area of  
4 said large-diameter single-crystal semiconductor block  
5 correspond to at most 65% of said cross-sectional area.

1 8. (original) The method of manufacturing single-crystal  
2 semiconductor blocks according to claim 1, wherein each of  
3 said small-diameter single-crystal semiconductor blocks is  
4 formed to have at least any of an orientation flat, an

5       index flat, and a notch for easy determination of its  
6       crystal orientation.

**[AMENDMENT FOLLOWS ON NEXT PAGE]**

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